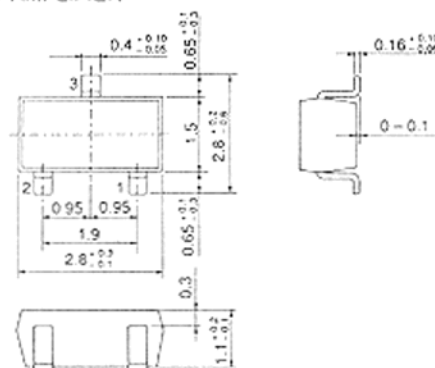


2SK323

SILICON N-CHANNEL JUNCTION FET
LOW FREQUENCY AMPLIFIER



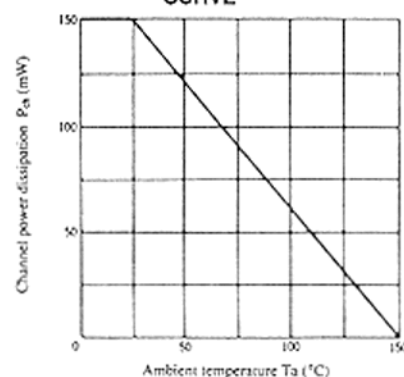
1. Drain
 2. Source
 3. Gate
- (Dimensions in mm)

(MPAK)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SK323	Unit
Gate to source voltage	V_{GS}	-40	V
Drain current	I_D	30	mA
Gate current	I_G	10	mA
Channel power dissipation	P_{ch}	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

MAXIMUM CHANNEL DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Gate to source breakdown voltage	$V_{(BR)GS}$	$I_G = -100\mu A, V_{DS} = 0$	-45	—	—	V
Gate cutoff current	I_{GSS}	$V_{GS} = -30V, V_{DS} = 0$	—	—	10	nA
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 10\mu A$	-0.13	-0.5	-1.5	V
Drain current	I_{DSS}^*	$V_{DS} = 10V, V_{GS} = 0$	1.6	—	12	mA
Forward transfer admittance	$ y_{fs} $	$V_{DS} = 10V, I_D = 3mA, f = 1kHz$	8	12	—	mS

* The 2SK323 is grouped by I_{DSS} as follows.

Grade	B	C	D	E
Mark	KB	KC	KD	KE
I_{DSS}	1.6 to 3.2	2.5 to 5	4 to 8	6 to 12

■ See characteristic curves of 2SK186.